

Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET

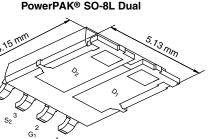
PRODUCT SUMMARY	
V _{DS} (V)	- 30
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.017
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.036
I _D (A)	- 30
Configuration	Dual

FEATURES

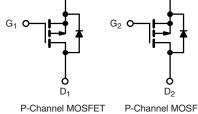
- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC







Bottom View



P-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ951EP-T1-GE3

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted	d)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 30		
Gate-Source Voltage		V _{GS} ± 20			
Continuous Drain Current	T _C = 25 °C ^a	1	- 30		
	T _C = 125 °C	I _D	- 28		
Continuous Source Current (Diode Conduction) ^a		I _S	- 30	А	
Pulsed Drain Current ^b		I _{DM}	- 120		
Single Pulse Avalanche Current	urrent		- 27		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	36.5	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	56	W	
	T _C = 125 °C	P_{D}	18.5	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature)e, f			260	-0	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	2.7	G/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							,
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0, I _D = - 250 μA	- 30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μA	- 1.5	- 2.0	- 2.5]
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = - 30 V	-	-	- 1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	μΑ
		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} = - 5 V	- 30	-	-	Α
		V _{GS} = - 10 V	I _D = - 7.5 A	-	0.014	0.017	
Drain Source On State Begintance	B	V _{GS} = - 10 V	I _D = - 7.5A, T _J = 125 °C	-	-	0.034	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 7.5 A, T _J = 175 °C	-	-	0.039	1
		V _{GS} = - 4.5 V	I _D = - 5 A	-	0.030	0.036	
Forward Transconductanceb	9 _{fs}	V _{DS} =	- 15 V, I _D = - 7.5 A	-	18		S
Dynamic ^b							
Input Capacitance	C _{iss}			-	1345	1680	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = - 10 V, f = 1 MHz	-	330	415	pF
Reverse Transfer Capacitance	C _{rss}			-	245	305	
Total Gate Charge ^c	Qg			-	33	50	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -9 \text{ A}$	-	5.5	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	9.4	-	
Gate Resistance	R _g		f = 1 MHz	3	6.31	10.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	18	
Rise Time ^c	t _r	$V_{DD} = 0$	- 15 V, $R_L = 1.66 \Omega$	-	12	18	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -9 A, V$	$V_{\rm GEN} = -10 \text{ V}, R_{\rm g} = 6 \Omega$	-	39	59	ns
Fall Time ^c	t _f	7		-	28	42	1
Source-Drain Diode Ratings and Chara	icteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 120	Α
Forward Voltage	V _{SD}	I _E = - 4.5 A, V _{GS} = 0		_	- 0.8	- 1.2	V

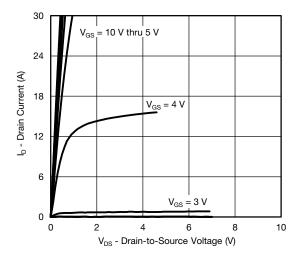
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

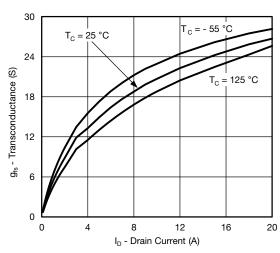
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



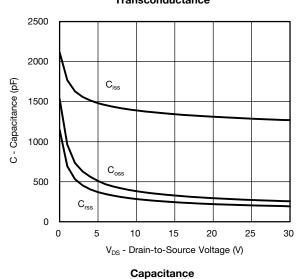
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



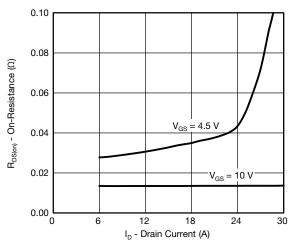
Output Characteristics



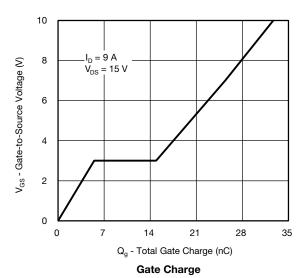
Transconductance



Transfer Characteristics

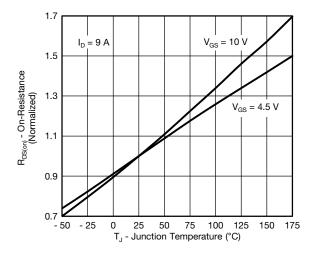


On-Resistance vs. Drain Current

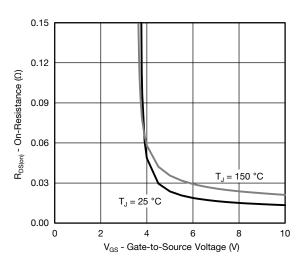




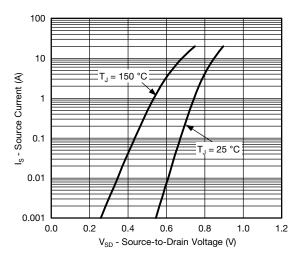
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



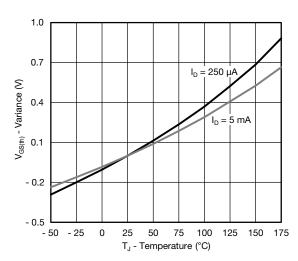
On-Resistance vs. Junction Temperature



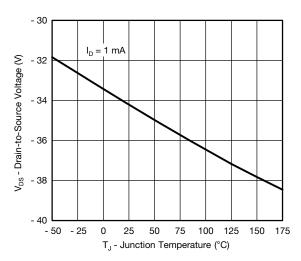
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



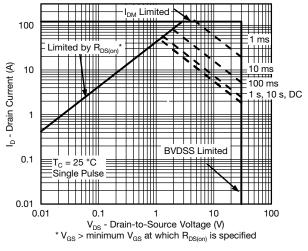
Threshold Voltage



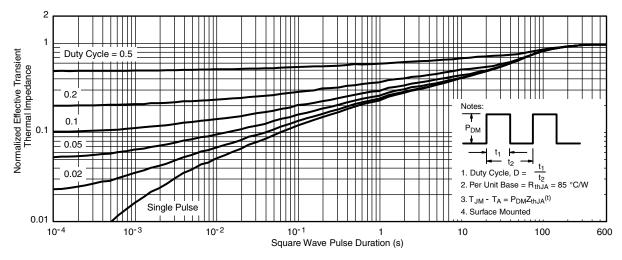
BVDSS vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

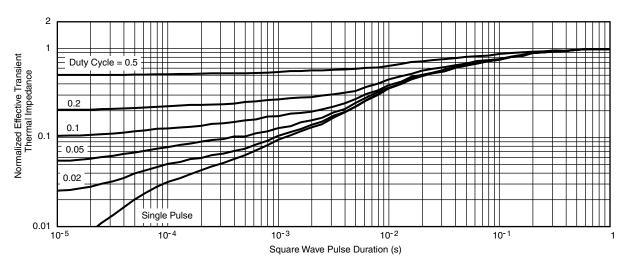


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

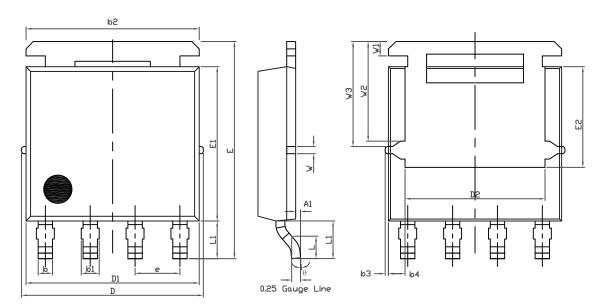
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

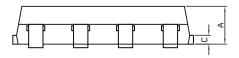
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

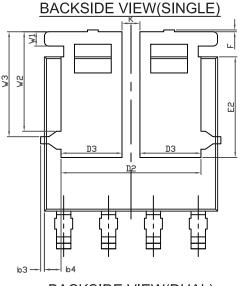
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PowerPAK® SO-8L Case Outline for Al Parts



TOPSIDE VIEW





BACKSIDE VIEW(DUAL)



DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	MAX			
Α	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W		0.23		0.009				
W1		0.41		0.016				
W2		2.82		0.111				
W3		2.96			0.117			
q	0°	-	10°	0°	-	10°		

ECN: C15-1203-Rev. A, 07-Sep-15

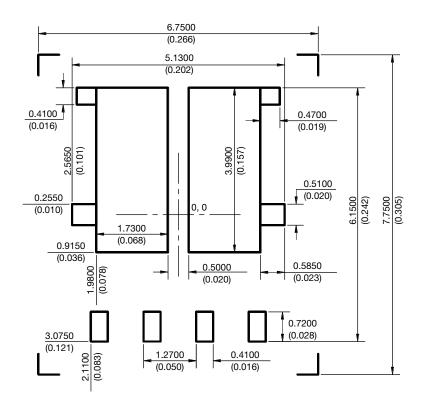
DWG: 6044

Note

· Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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